

To all our customers

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Renesas Technology Corp.
Customer Support Dept.
April 1, 2003

Cautions

Keep safety first in your circuit designs!

1. Renesas Technology Corporation puts the maximum effort into making semiconductor products better and more reliable, but there is always the possibility that trouble may occur with them. Trouble with semiconductors may lead to personal injury, fire or property damage.

Remember to give due consideration to safety when making your circuit designs, with appropriate measures such as (i) placement of substitutive, auxiliary circuits, (ii) use of nonflammable material or (iii) prevention against any malfunction or mishap.

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2SD2263

Silicon NPN Epitaxial

RENESAS

ADE-208-1167 (Z)

1st. Edition

Mar. 2001

Application

Low frequency power amplifier

Features

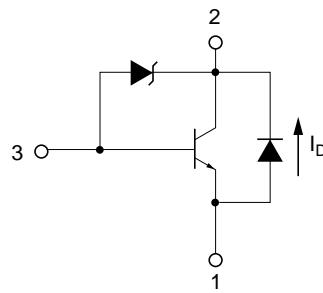
- Build in zener diode for surge absorbt.
- Suitable for relay drive with small power loss.

Outline

TO-92 (1)



1. Emitter
2. Collector
3. Base



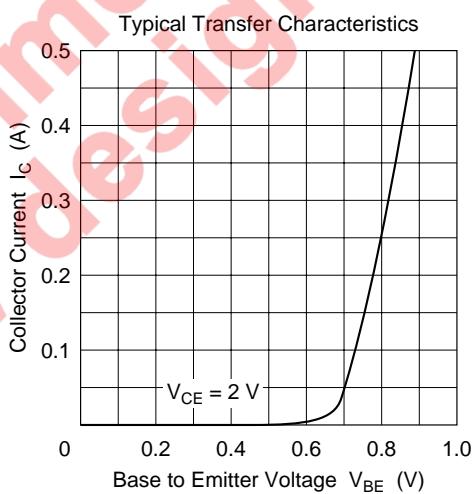
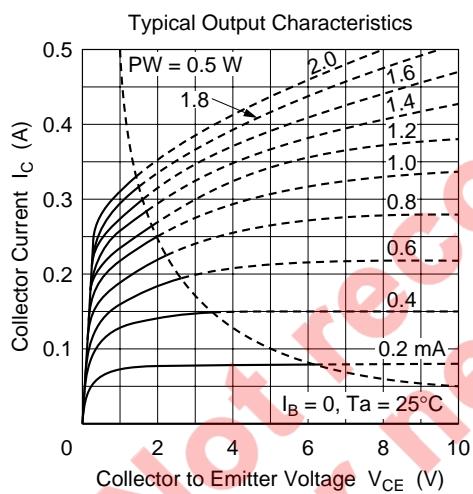
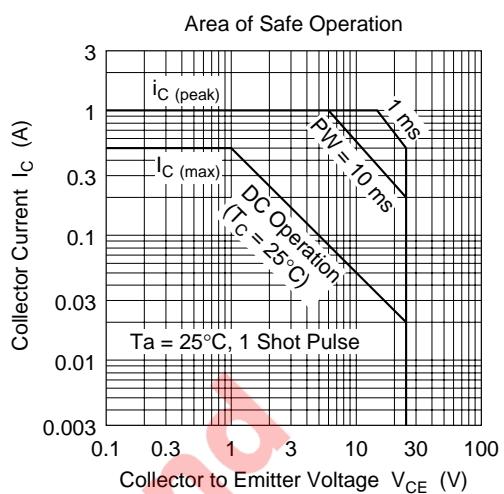
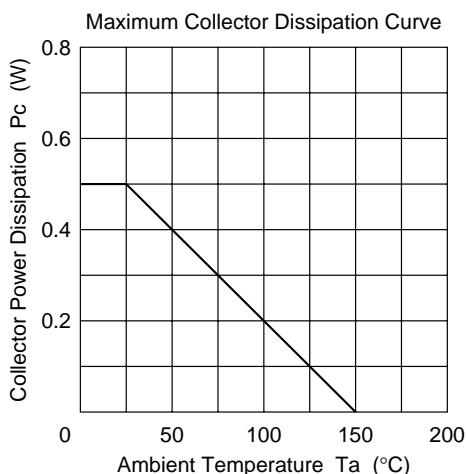
Absolute Maximum Ratings (Ta = 25°C)

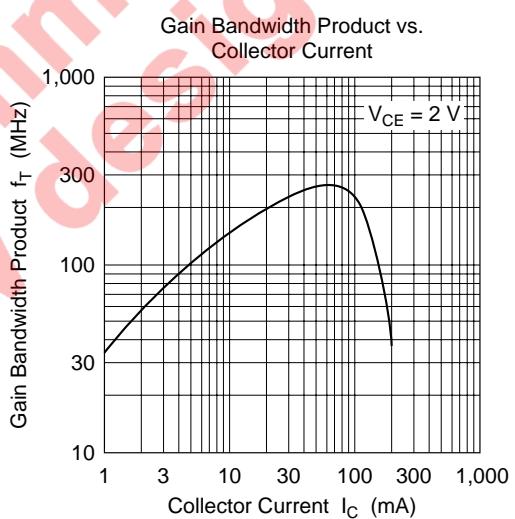
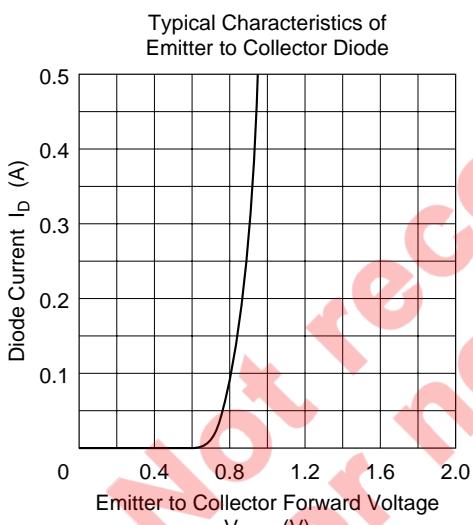
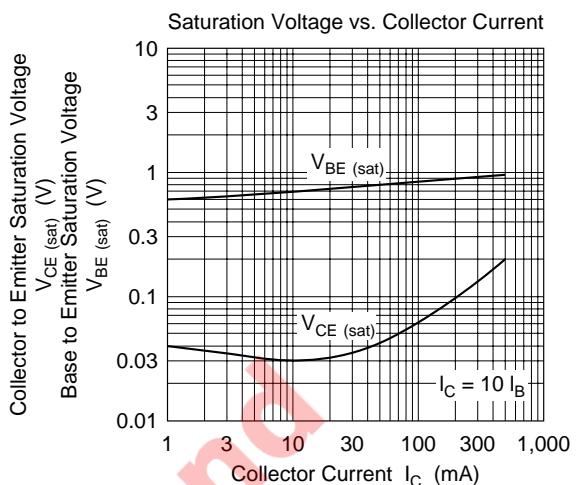
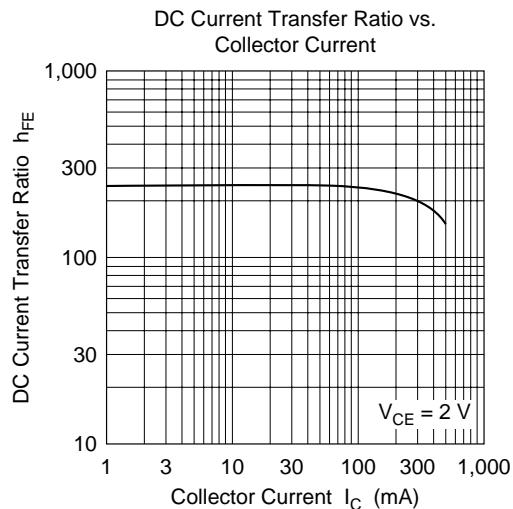
Item	Symbol	Ratings	Unit
Collector to base voltage	V _{CBO}	25	V
Collector to emitter voltage	V _{CEO}	25	V
Emitter to base voltage	V _{EBO}	6	V
Collector current	I _C	0.5	A
Collector peak current	i _{C(peak)}	1.0	A
E to C diode current	I _D	0.5	A
Collector power dissipation	P _C	0.5	W
Junction temperature	T _J	150	°C
Storage temperature	T _{STG}	-55 to +150	°C

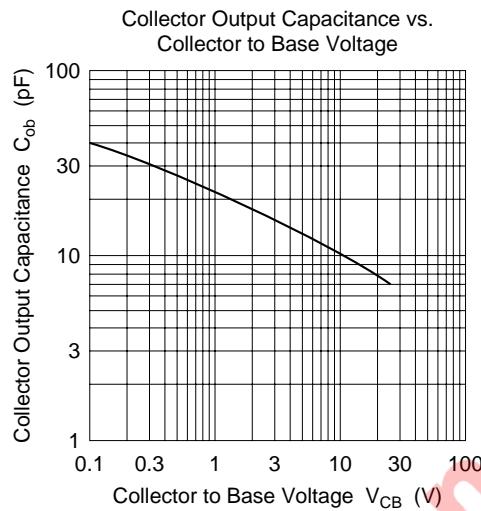
Electrical Characteristics (Ta = 25°C)

Item	Symbol	Min	Typ	Max	Unit	Test conditions
Collector to base breakdown voltage	V _{(BR)CBO}	25	—	—	V	I _C = 10 µA, I _E = 0
Collector to emitter breakdown voltage	V _{(BR)CEO}	25	—	35	V	I _C = 1 mA, R _{BE} = ∞
Collector to emitter sustaining voltage	V _{CEO(sus)}	26	—	36	V	I _C = 0.5 A, R _{BE} = ∞, L = 20 mH
Emitter to base breakdown voltage	V _{(BR)EBO}	6	—	—	V	I _E = 10 µA, I _C = 0
Collector cutoff current	I _{CBO}	—	—	0.2	µA	V _{CB} = 20 V, I _E = 0
	I _{CEO}	—	—	0.5	µA	V _{CE} = 20 V, R _{BE} = ∞
Emitter cutoff current	I _{EBO}	—	—	0.2	µA	V _{EB} = 5 V, I _E = 0
DC current transfer ratio	h _{FE1}	100	—	500		V _{CE} = 2 V, I _C = 50 mA ^{*1}
	h _{FE2}	50	—	—		V _{CE} = 2 V, I _C = 0.5 A ^{*1}
Collector to emitter saturation voltage	V _{CE(sat)}	—	—	0.5	V	I _C = 0.5 A ^{*1} , I _B = 50 mA
E to C diode forward voltage	V _D	—	—	1.2	V	I _E = 0.5 A ^{*1}

Note: 1. Pulse test



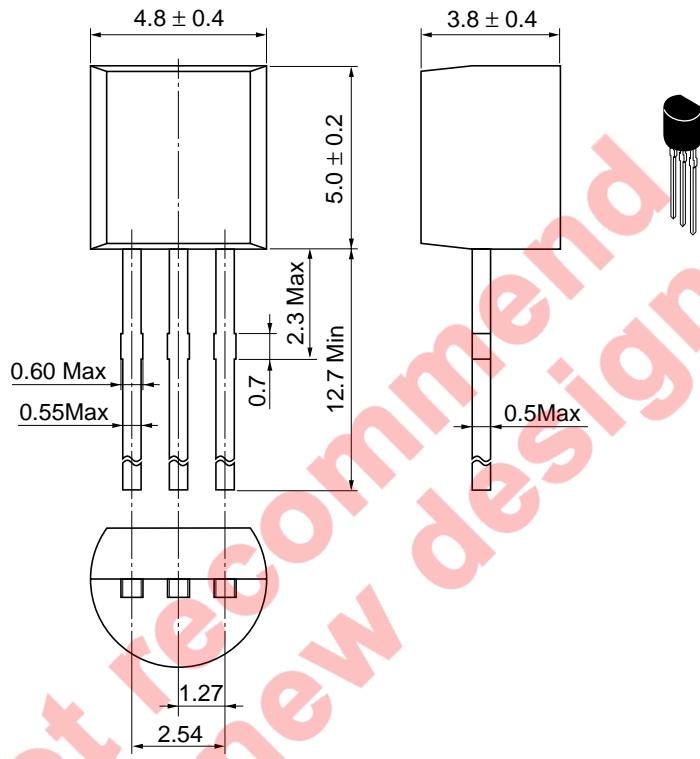




Not recommended
for new design

Package Dimensions

As of January, 2001
Unit: mm



Hitachi Code	TO-92 (1)
JEDEC	Conforms
EIAJ	Conforms
Mass (reference value)	0.25 g

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